

The documentation and process conversion measures necessary to comply with this revision shall be completed by 7 May 2008.

INCH-POUND

MIL-PRF-19500/369F
7 February 2008
SUPERSEDING
MIL-PRF-19500/369E
30 January 2006

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, TRANSISTOR, NPN, SILICON, POWER,
TYPE 2N3441, JAN, JANTX, AND JANTXV

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and MIL-PRF-19500.

1. SCOPE

* 1.1 Scope. This specification covers the performance requirements for NPN, silicon, power transistor. Three levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1 (similar to TO-66).

* 1.3 Maximum ratings. Unless otherwise specified, $T_C = +25^\circ\text{C}$.

P_T		$R_{\theta JA}$	$R_{\theta JC}$ (2)	V_{CBO}	V_{CEO}	V_{EBO}	V_{CER}	I_B	I_C	T_{STG} and T_J
$T_A = +25^\circ\text{C}$ (1)	$T_C = +25^\circ\text{C}$ (1)									
<u>W</u>	<u>W</u>	<u>$^\circ\text{C/W}$</u>	<u>$^\circ\text{C/W}$</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>$^\circ\text{C}$</u>
3.0	25	58.5	3	160	140	7.0	150	2.0	3.0	-65 to +200

(1) For derating see figures 2 and 3.

(2) For thermal impedance see figure 4.

Comments, suggestions, or questions on this document should be addressed to Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dsc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <http://assist.daps.dla.mil/>.

1.4 Primary electrical characteristics.

	h_{FE2} $V_{CE} = 4 \text{ V dc}$ $I_C = 0.5 \text{ A dc}$	$ h_{fe} $ $V_{CE} = 4 \text{ V dc}$ $I_C = 0.5 \text{ A dc}$ $f = 100 \text{ kHz}$	h_{fe} $V_{CE} = 4 \text{ V dc}$ $I_C = 0.5 \text{ A dc}$	$V_{CE(sat)}$ $I_C = 0.5 \text{ A dc}$ $I_B = 50 \text{ mA dc}$	Pulse response	
					t_{on}	t_{off}
				<u>V dc</u>	<u>μs</u>	<u>μs</u>
Min	25	4	15			
Max	100	40	100	1	8	15

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Copies of these documents are available online at <http://assist.daps.dla.mil/quicksearch> or <http://assist.daps.dla.mil> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

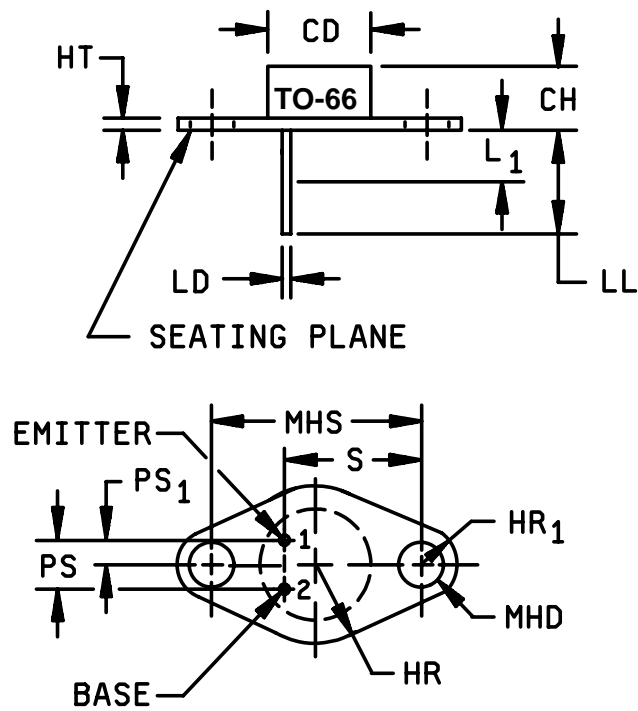
2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.



* FIGURE 1. Physical dimensions (similar to TO-66).

Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.470	.500	11.94	12.70	
CH	.250	.340	6.35	8.64	
HR		.350		8.89	
HR ₁	.115	.145	2.92	3.68	
HT	.050	.075	1.27	1.91	
LD	.028	.034	0.71	0.86	4, 6
LL	.360	.500	9.14	12.70	
L ₁		.050		1.27	6
MHD	.142	.152	3.61	3.86	4
MHS	.958	.962	24.33	24.43	
PS	.190	.210	4.83	5.33	3
PS ₁	.093	.107	2.36	2.72	3
S	.570	.590	14.48	14.99	

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. These dimensions should be measured at points .050 inch (1.27 mm) \pm .005 inch (0.13 mm) - 0 inch below seating plane. When gauge is not used, measurement will be made at the seating plane.
4. Two places.
5. The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
6. Lead diameter shall not exceed twice LD within L₁.
7. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.
8. Pin 1 is the emitter and pin 2 is the base. The collector shall be electrically connected to the case.

* FIGURE 1. Physical dimensions - Continued.

3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figure 1.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I.

3.6 Electrical test requirements. The electrical test requirements shall be as specified in table I.

3.7 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4 and table I).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table II tests, the tests specified in table II herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

* 4.3 Screening (JANTX and JANTXV levels only). Screening shall be in accordance with table E-IV of MIL-PRF-19500 and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table E-IV of MIL-PRF-19500)	Measurement
	JANTX and JANTXV levels
(1) 3c	Thermal impedance, see 4.3.2.
9	Not applicable.
11	I_{CEX1} and h_{FE3} .
12	Burn-in (see 4.3.1).
13	ΔI_{CEX1} = 100 percent of initial value or 100 μ A dc; whichever is greater. Δh_{FE3} = ± 25 percent Subgroup 2 table I herein.

(1) Shall be performed anytime after temperature cycling, screen 3a; and does not need to be repeated in screening requirements.

4.3.1 Power burn-in conditions. Power burn-in conditions are as follows:

- a. $T_A = +30^\circ\text{C} \pm 5^\circ\text{C}$.
- b. $V_{CB} \geq 100$ V dc.
- c. $T_J = +187.5^\circ\text{C} \pm 12.5^\circ\text{C}$.

NOTE: No heatsink or forced air-cooling on the devices shall be permitted.

4.3.2 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3161 of MIL-STD-750 using the guidelines in that method for determining I_M , I_H , t_H , t_{SW} , (and V_H where appropriate). Measurement delay time (t_{MD}) = 70 μ s max. See table II, group E, subgroup 4 herein.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500, and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500, and table I herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein.

* 4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VIB (JAN, JANTX and JANTXV) of MIL-PRF-19500, and as follows. Electrical measurements (end-points) shall be in accordance with the applicable inspections of table I, subgroup 2 herein. Delta measurements shall be in accordance with table III herein.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
B3	1027	$T_J = +187.5^\circ\text{C} \pm 12.5^\circ\text{C}$, $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$; $V_{CB} > 24 \text{ V dc}$.
B6	1032	$T_{STG} = +200^\circ\text{C}$
B7	3053	Load condition C; (unclamped inductive load), (see safe operating area figure herein) $T_C = +25^\circ\text{C}$, duty cycle ≤ 10 percent, $R_1 = 0.1 \Omega$, $t_r = t_f \leq 500 \text{ ns}$. Test 1. $t_p = 10 \text{ ms}$, (vary to obtain I_G), $V_{BB2} = 1.5 \text{ V dc}$, $R_{BB1} = 5 \Omega$, $L = 5 \text{ mH}$ (two Super Electric Corporation type S16884 in parallel or equivalent, dc resistance $\leq 0.1 \Omega$), $V_{BB1} = 10 \text{ V}$, $R_{BB2} = 100 \Omega$, $V_{CC} = 10 \text{ V dc}$, $I_C = 3 \text{ A dc}$. Test 2. $t_p = 10 \text{ ms}$, (vary to obtain I_C), $V_{BB2} = 1.5 \text{ V dc}$, $R_{BB1} = 50 \Omega$, $L = 100 \text{ mH}$ (two Traid C48U in series: 80 mH winding and 20 mH winding or equivalent, dc resistance $\leq 0.1 \Omega$), $V_{BB1} = 10 \text{ V}$, $R_{BB2} = 100 \Omega$, $V_{CC} = 10 \text{ V dc}$, $I_C = 0.5 \text{ A dc}$.
B7	3053	Load condition B (see safe operating figure herein), $T_A = +25^\circ\text{C}$, $L = 20 \text{ mH}$ (Traid C48U or equivalent, dc resistance $\leq 0.1 \Omega$), $V_{CC} = 50 \text{ V dc}$, $I_C = 3 \text{ A dc}$, $R_{BB1} = 5 \Omega$, $V_{BB1} = 10 \text{ V dc}$, clamped voltage = 140 V dc, $R_{BB2} = 100 \Omega$, $V_{BB2} = 1.5 \text{ V dc}$.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the test and conditions specified for subgroup testing in table E-VII of MIL-PRF-19500, and as follows. Electrical measurements (end-points) shall be in accordance with the applicable inspections of table I, subgroup 2 herein. Delta measurements shall be in accordance with table III herein.

<u>Subgroup</u>	<u>Method</u>	<u>Conditions</u>
C2	1056	Test condition B.
C2	2036	Test condition A, weight - 3 pounds, 15 seconds.
C5	3131	Thermal resistance, see 4.3.2, $R_{\theta JC} = 3^\circ\text{C/W}$.
C6	1026	$T_J = +187.5^\circ\text{C} \pm 12.5^\circ\text{C}$, $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$, $V_{CB} \geq 24 \text{ V dc}$.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-IX of MIL-PRF-19500 and as specified in table II herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2. Delta measurements shall be in accordance with table III herein.

4.5 Methods of inspection. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

TABLE I. Group A inspection.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Thermal impedance 2/	3131	See 4.3.2.	$Z_{\theta JX}$			°C/W
Breakdown voltage, collector to base	3011	Bias condition D, pulsed (see 4.5.1), $I_C = 100 \text{ mA dc}$	$V_{(BR)CEO}$	140		V dc
Breakdown voltage, collector to emitter	3011	Bias condition B, $I_C = 100 \text{ mA dc}$, $R_{BE} = 100\Omega$, pulsed (see 4.5.1)	$V_{(BR)CER}$	150		V dc
Breakdown voltage, collector to emitter	3011	Bias condition A, $I_C = 100 \text{ mA dc}$, $V_{BE} = -1.5 \text{ V dc}$, pulsed (see 4.5.1)	$V_{(BR)CEX}$	160		V dc
Emitter to base current	3061	Bias condition D, $V_{EB} = 7.0 \text{ V dc}$	I_{EBO}		1	mA dc
Collector - emitter cutoff current	3041	Bias condition A, $V_{BE} = -1.5 \text{ V dc}$, $V_{CE} = 140 \text{ V dc}$	I_{CEX1}		1	mA dc
Base emitter voltage (nonsaturated)	3066	Test condition B; pulsed (see 4.5.1), $I_C = 0.5 \text{ A dc}$, $V_{CE} = 4.0 \text{ V dc}$	V_{BE}		1.7	V dc
Collector to emitter voltage (saturated)	3071	Pulsed (see 4.5.1), $I_C = 0.5 \text{ A dc}$, $I_B = 50 \text{ mA dc}$	$V_{CE(sat)}$		1	V dc
Forward current transfer ratio	3076	$V_{CE} = 4 \text{ V dc}$, $I_C = 50 \text{ mA dc}$, pulsed (see 4.5.1)	h_{FE1}	50		
Forward current transfer ratio	3076	$V_{CE} = 4 \text{ V dc}$, $I_C = 0.5 \text{ A dc}$, pulsed (see 4.5.1)	h_{FE2}	25	100	
Forward current transfer ratio	3076	$V_{CE} = 4 \text{ V dc}$, $I_C = 1 \text{ A dc}$, pulsed (see 4.5.1)	h_{FE3}	10		

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection 1/	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 3</u>						
High temperature operation:		T _A = +150°C				
Collector to emitter cutoff current	3041	Bias condition A, V _{BE} = -1.5 V dc, V _{CE} = 140 V dc	I _{CEX}		5	mA dc
Low temperature operation		T _A = -65°C				
Forward current transfer ratio	3076	V _{CE} = 4 V dc, I _C = 0.5 A dc, pulsed (see 4.5.1)	h _{FE4}	15		
<u>Subgroup 4</u>						
Pulse response transfer ratio	3251	Test condition A, except test circuit and pulse requirements in accordance with figure 5 herein.				
Turn-on time		V _{CC} = 30 V dc, (see figure 5); I _C = 0.5 A dc, I _B = 50 mA dc	t _{on}		8	μs
Turn-off time		V _{CC} = 30 V dc, (see figure 5); I _C = 0.5 A dc, I _{B1} = -I _{B2} = 50 mA dc	t _{off}		15	μs
Magnitude of common emitter small-signal short-circuit forward current transfer ratio	3306	V _{CE} = 4 V dc, I _C = 0.5 A dc, f = 100 kHz	h _{fe}	4	40	
Open circuit (output capacitance)	3236	V _{CB} = 10 V dc, I _E = 0, 100 kHz ≤ f ≤ 1 MHz	C _{obo}		300	pF
Small-signal short-circuit forward-current transfer ratio	3206	V _{CE} = 4 V dc, I _C = 0.5 A dc	h _{fe}	15	100	

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 5</u>						
Safe operating area (dc operation)	3051	$T_C = +25^{\circ}\text{C}$, $t = 1 \text{ s}$, 1 cycle, see figure 6 and 7.				
Test 1		$I_C = 3 \text{ A dc}$, $V_{CE} = 8.33 \text{ V dc}$				
Test 2		$I_C = 833 \text{ mA dc}$, $V_{CE} = 30 \text{ V dc}$				
Test 3		$I_C = 178.5 \text{ mA dc}$, $V_{CE} = 140 \text{ V dc}$				
Electrical measurements		See table I, subgroup 2 herein.				
<u>Subgroups 6 and 7</u>						
Not applicable						

1/ For sampling plan see MIL-PRF-19500.

2/ This test required for the following end-point measurements only:

* Group B, subgroups 2 and 3 (JAN, JANTX and JANTXV).

Group C, subgroup 2 and 6.

Group E, subgroup 1.

* TABLE II. Group E inspection (all quality levels) for qualification only.

Inspection	MIL-STD-750		Sample plan
	Method	Conditions	
<u>Subgroup 1</u>			45 devices, c = 0
Temperature cycling	1051	500 cycles	
Hermetic seal	1071		
Fine leak			
Gross leak			
Electrical measurements		See table I, subgroup 2 and table III.	
<u>Subgroup 2</u>			45 devices, c = 0
Blocking life	1048	Test temperature = +125°C; V _{CB} = 80 percent of rated, T = 1,000 hours.	
Electrical measurements		See table I, subgroup 2 and table III.	
<u>Subgroup 4</u>			sample size N/A
Thermal impedance curves		See MIL-PRF-19500.	
<u>Subgroup 6</u>			3 devices
Electrostatic discharge (ESD)	1020	Testing not required for class 3 listing. For non-sensitive listing, testing is required to prove capacity.	
<u>Subgroup 8</u>			45 devices c = 0
Reverse stability	1033	Condition B.	

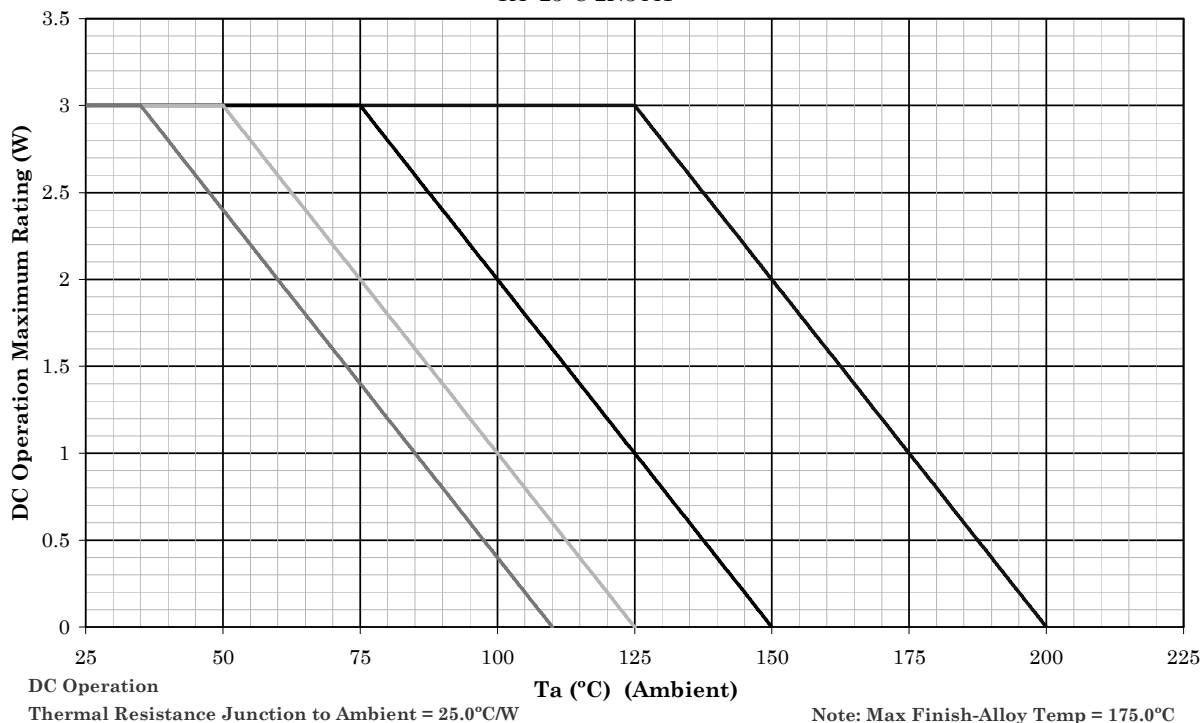
TABLE III. Groups B, C, and E delta measurements. 1/ 2/ 3/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Collector to emitter cutoff current	3041	Bias condition A, $V_{BE} = 1.5 \text{ V dc}$, $V_{CE} = 140 \text{ V dc}$	ΔI_{CEX1}	100 percent of initial value or $100 \mu\text{A dc}$, whichever is greater.		
2.	Forward current transfer ratio	3076	$V_{CE} = 4 \text{ V dc}$, $I_C = 0.5 \text{ A dc}$, pulsed (see 4.5.1)	Δh_{FE2}	± 25 percent change in initial recorded value.		

- * 1/ The delta measurements for table E-VIB (JAN, JANTX and JANTXV) of MIL-PRF-19500 are as follows:
a. Subgroup 3, see table III herein, steps 1 and 2.
b. Subgroup 6, see table III herein, step 2.
- * 2/ The delta measurements for table E-VII (JAN, JANTX and JANTXV) of MIL-PRF-19500 are as follows:
Subgroup 6, see table III herein, steps 1 and 2.
- 3/ The delta measurements for table E-IX of MIL-PRF-19500 are as follows: Subgroups 1 and 2, see table III herein, steps 1 and 2.

Temperature-Power Derating Curve

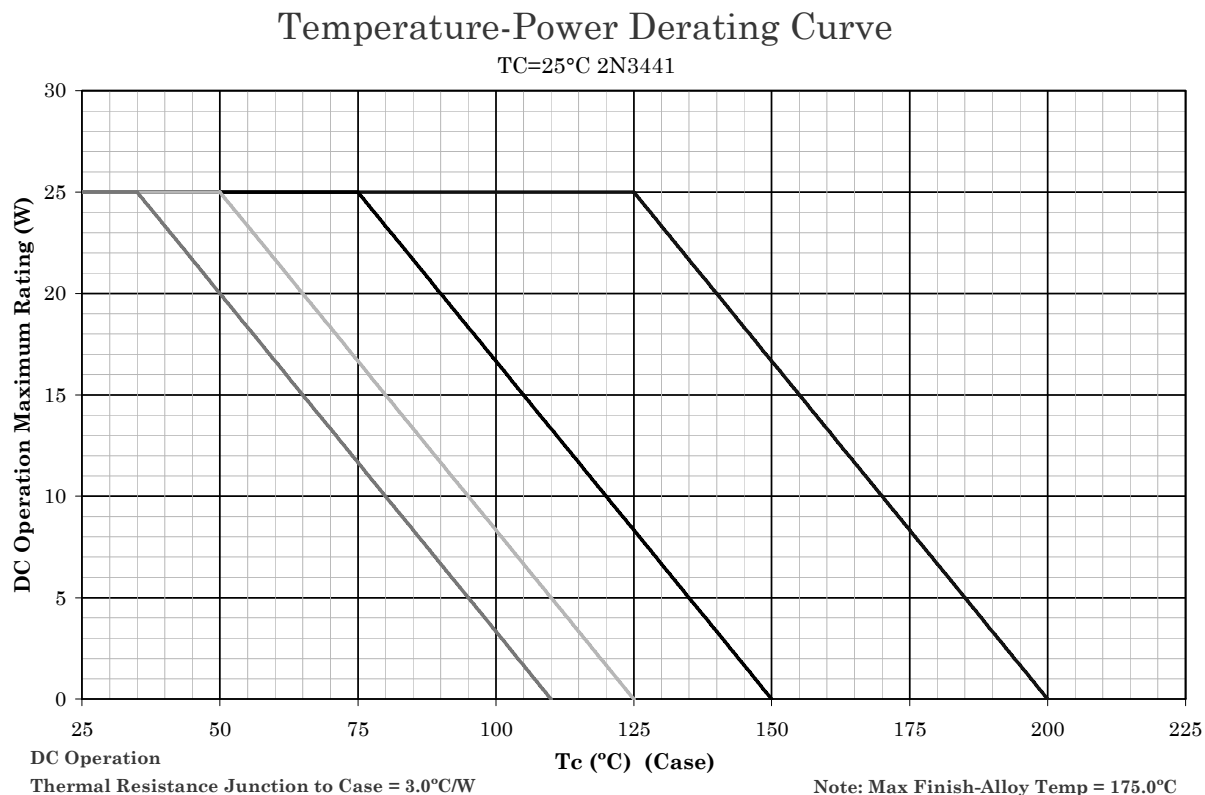
TA=25°C 2N3441



NOTES:

1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq +200^\circ\text{C}$) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$ where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq +125^\circ\text{C}$ and $+110^\circ\text{C}$ to show power rating where most users want to limit T_J in their application.

* FIGURE 2. Temperature-power derating for 2N3441, $R_{\theta JA} = 25^\circ\text{C/W}$ (TO-66).

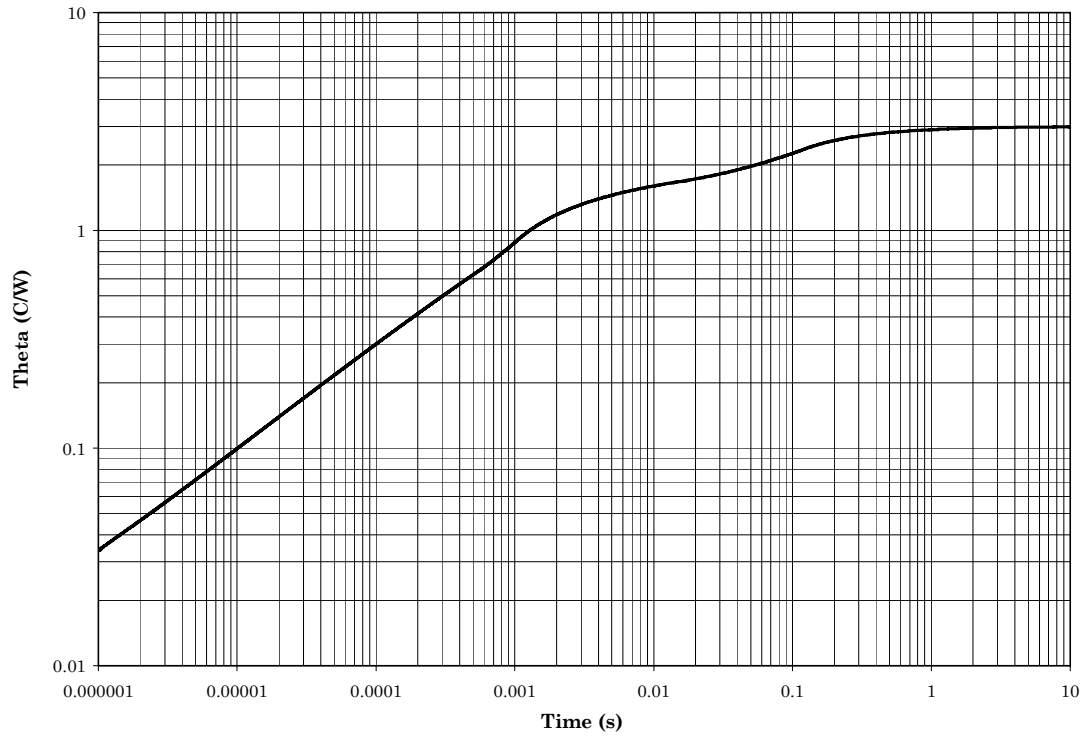


NOTES:

1. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq +200^\circ\text{C}$) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$ where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at $T_J \leq +125^\circ\text{C}$ and $+110^\circ\text{C}$ to show power rating where most users want to limit T_J in their application.

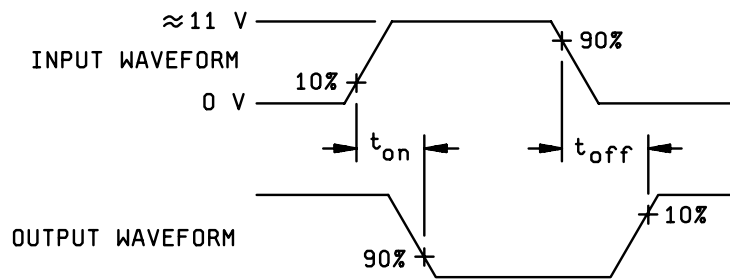
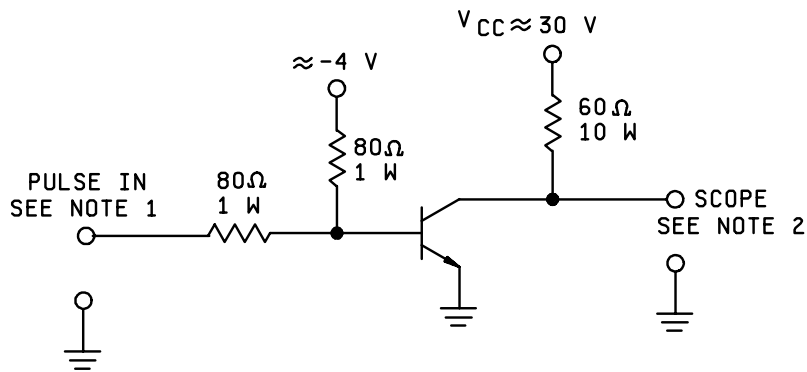
* FIGURE 3. Temperature-power derating for 2N3441, $R_{\theta JC} = 3^\circ\text{C/W}$ (TO-66).

Maximum Thermal Impedance



$T_C = +25^\circ\text{C}$, thermal resistance $R_{\theta JC} = 3^\circ\text{C/W}$ at $T_C +25^\circ\text{C}$.

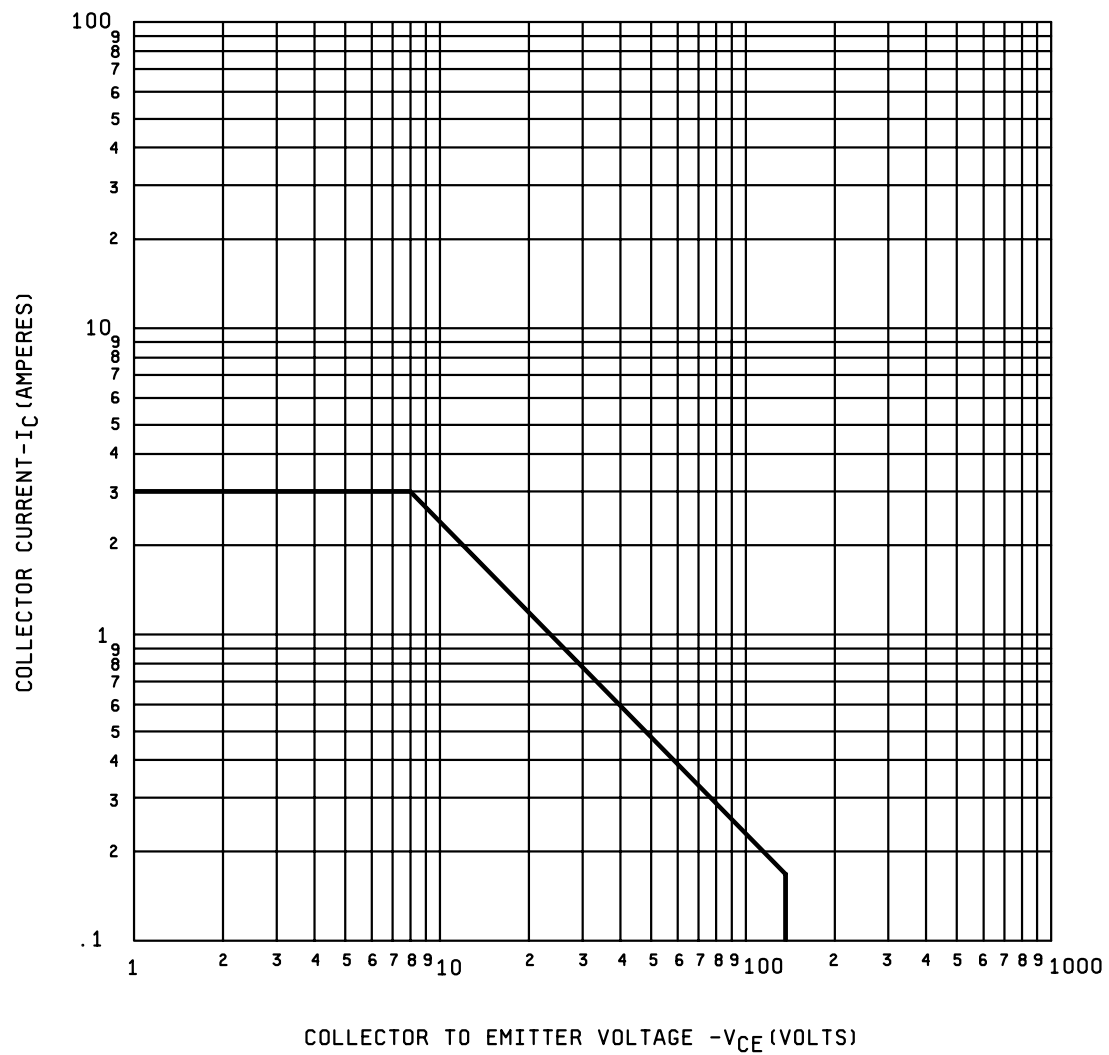
FIGURE 4. Thermal impedance graph for 2N3441, (TO-66).



NOTES:

1. The rise time (t_r) and fall time (t_f) of the applied pulse shall be each ≤ 20 ns; duty cycle ≤ 2 percent; generator source impedance shall be 50Ω ; pulse width = $20\ \mu\text{s}$.
2. Output sampling oscilloscope: $Z_{in} \geq 100\ \text{k}\Omega$; $C_{in} \leq 50\ \text{pF}$; rise time ≤ 20 ns.

FIGURE 5. Pulse response test circuit.

FIGURE 6. Maximum safe operating area graph (continuous dc).

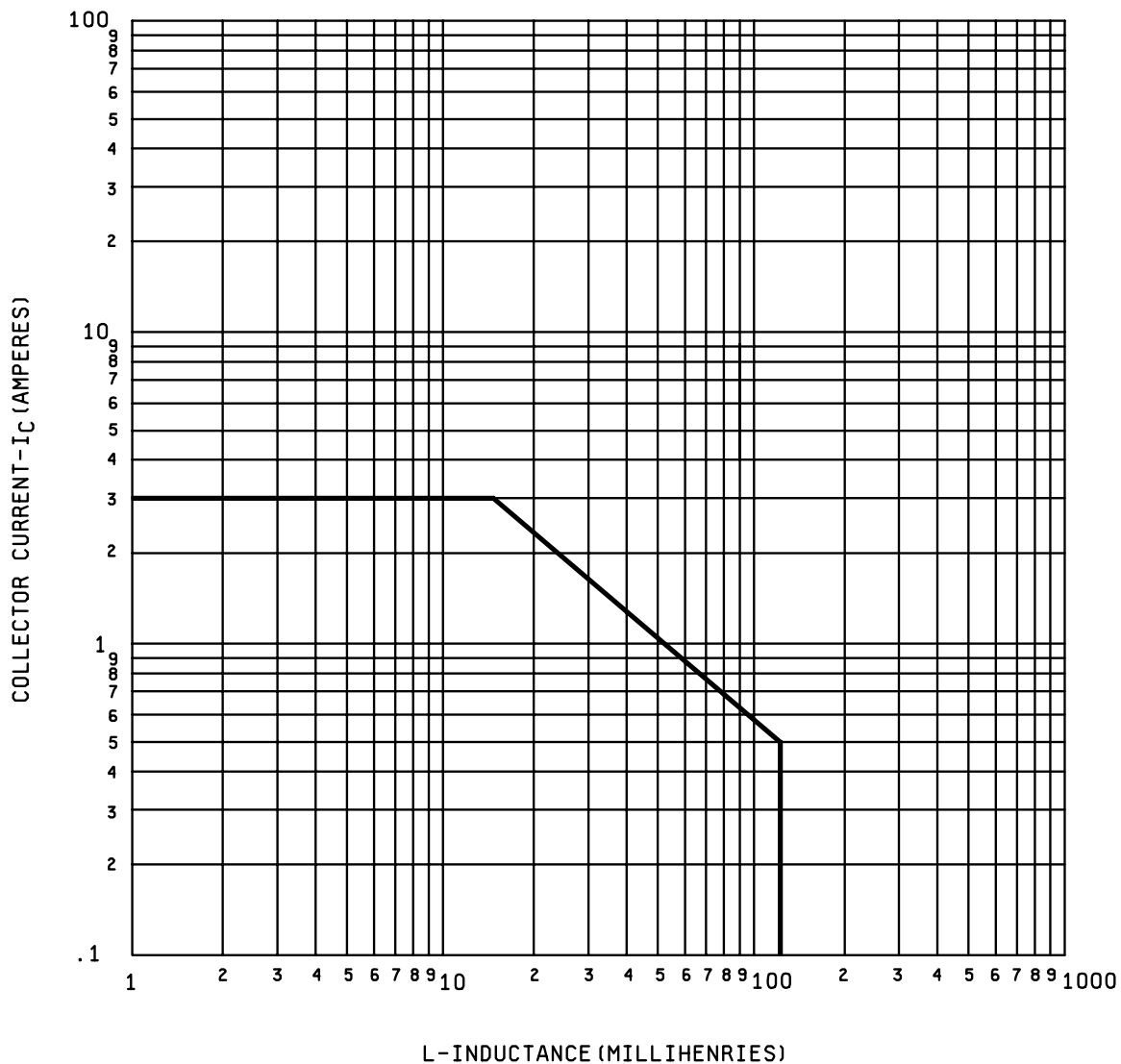


FIGURE 7. Safe operating area for switching between saturation and cutoff (unclamped inductive load) see subgroup 5 of table I.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

* (This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

* 6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- d. Product assurance level and type designator.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil.

6.4 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:
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Preparing activity:
 DLA - CC

(Project 5961-2007-098)

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